

Complementary Silicon Plastic Power Transistors

... designed for use in general purpose amplifier and switching applications.

- Collector – Emitter Saturation Voltage —
 $V_{CE(sat)} = 1.5 \text{ Vdc (Max) @ } I_C = 6.0 \text{ Adc}$
- Collector Emitter Sustaining Voltage —
 $V_{CEO(sus)} = 80 \text{ Vdc (Min) — BD243B, BD244B}$
 $= 100 \text{ Vdc (Min) — BD243C, BD244C}$
- High Current Gain Bandwidth Product
 $f_T = 3.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Compact TO-220 AB Package

MAXIMUM RATINGS

Rating	Symbol	BD243B BD244B	BD243C BD244C	Unit
Collector–Emitter Voltage	V_{CEO}	80	100	Vdc
Collector–Base Voltage	V_{CB}	80	100	Vdc
Emitter–Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak	I_C	6 10		Adc
Base Current	I_B	2.0		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	65 0.52		Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.92	°C/W

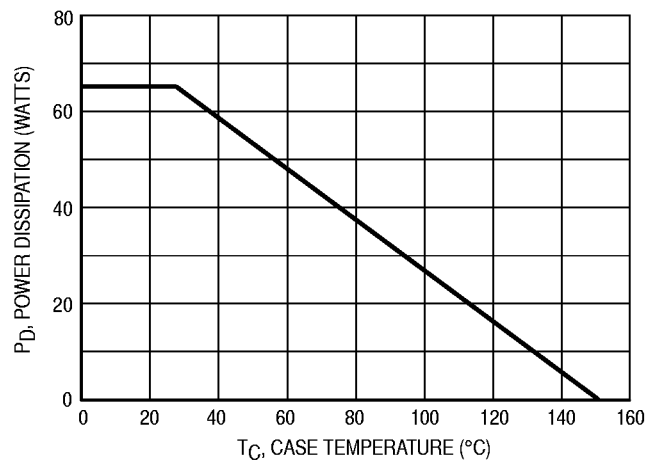


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7



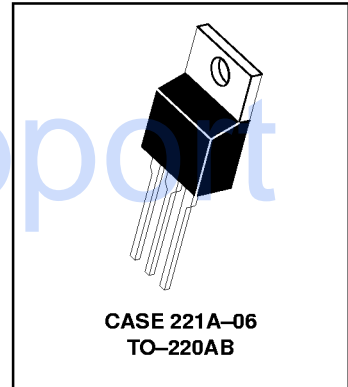
NPN
BD243B

BD243C*
PNP
BD244B

BD244C*

*Motorola Preferred Device

6 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
80–100 VOLTS
65 WATTS



BD243B BD243C BD244B BD244C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (1) ($I_C = 30\text{ mA}$, $I_B = 0$)	$V_{CE(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	0.7	mA
Collector Cutoff Current ($V_{CE} = 80\text{ Vdc}$, $V_{EB} = 0$) ($V_{CE} = 100\text{ Vdc}$, $V_{EB} = 0$)	I_{CES}	— —	400 400	μA
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	1.0	mA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 0.3\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 3.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	30 15	— —	—
Collector–Emitter Saturation Voltage ($I_C = 6.0\text{ A}$, $I_B = 1.0\text{ A}$)	$V_{CE(sat)}$	—	1.5	Vdc
Base–Emitter On Voltage ($I_C = 6.0\text{ A}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	—	2.0	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product (2) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	3.0	—	MHz
Small–Signal Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	20	—	—

(1) Pulse Test: Pulsewidth $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

(2) $f_T = h_{fe} \cdot f_{test}$

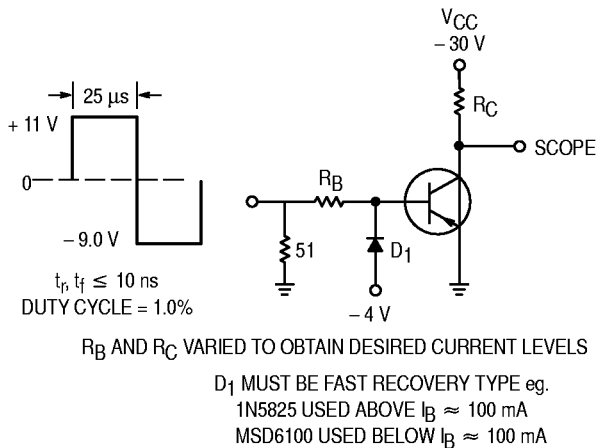


Figure 2. Switching Time Test Circuit

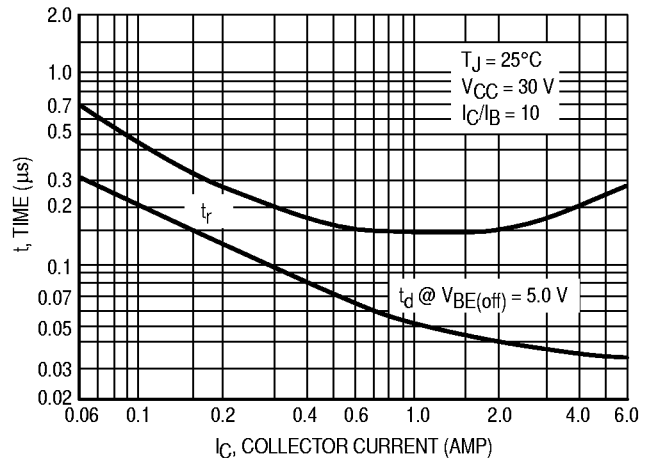


Figure 3. Turn–On Time

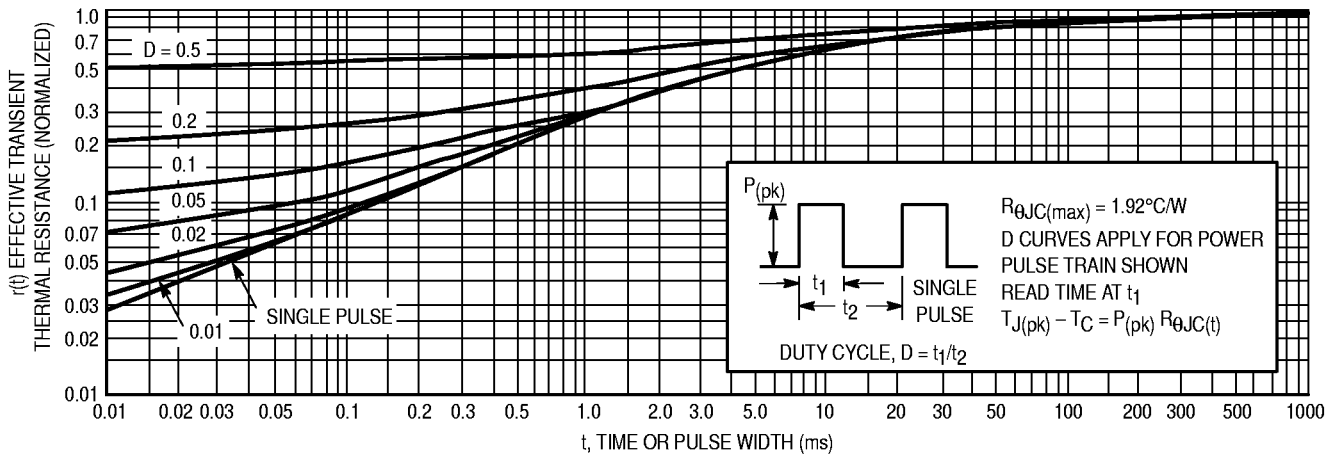


Figure 4. Thermal Response

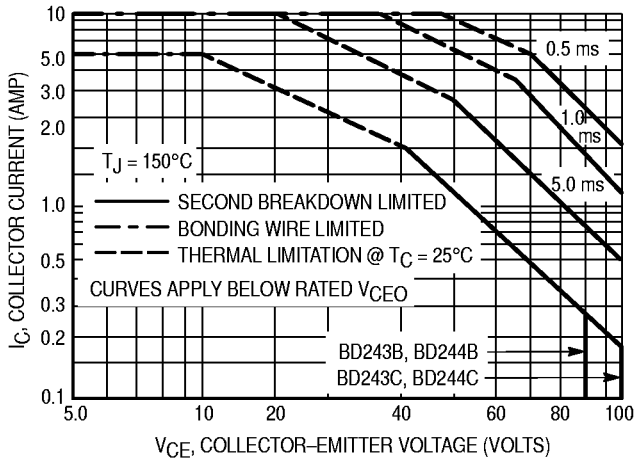


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ C$, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

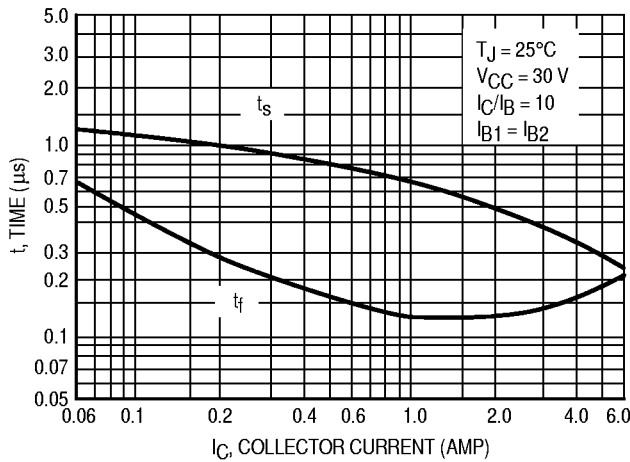


Figure 6. Turn-Off Time

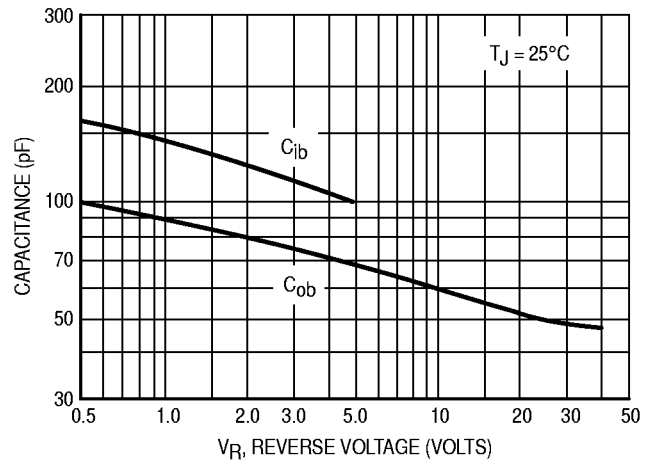


Figure 7. Capacitance

BD243B BD243C BD244B BD244C

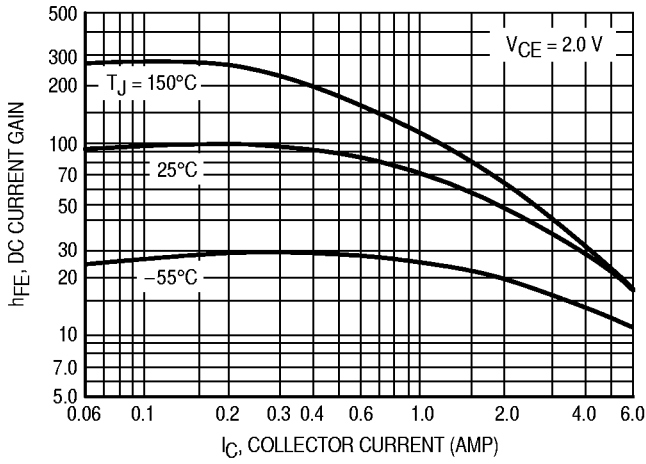


Figure 8. DC Current Gain

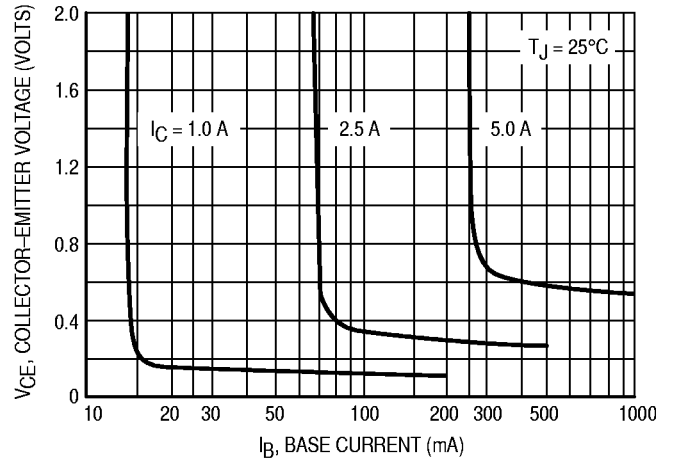


Figure 9. Collector Saturation Region

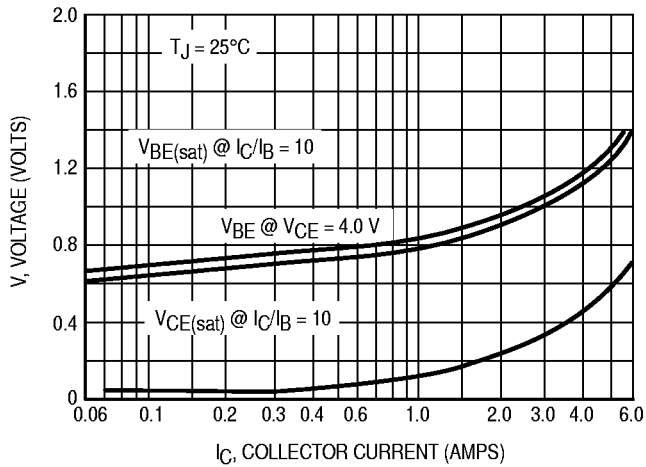


Figure 10. "On" Voltages

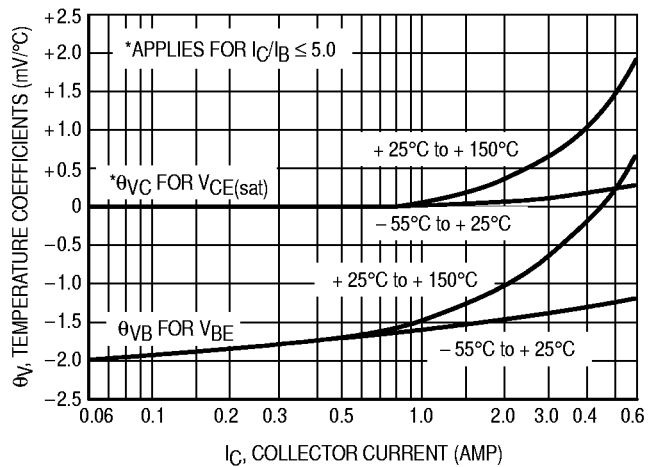


Figure 11. Temperature Coefficients

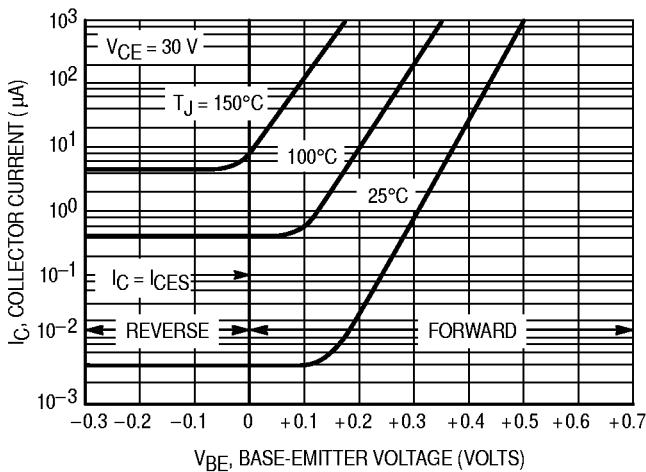


Figure 12. Collector Cut-Off Region

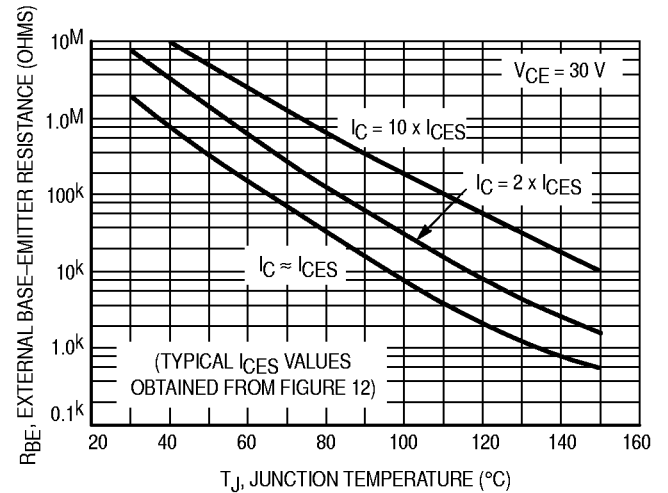
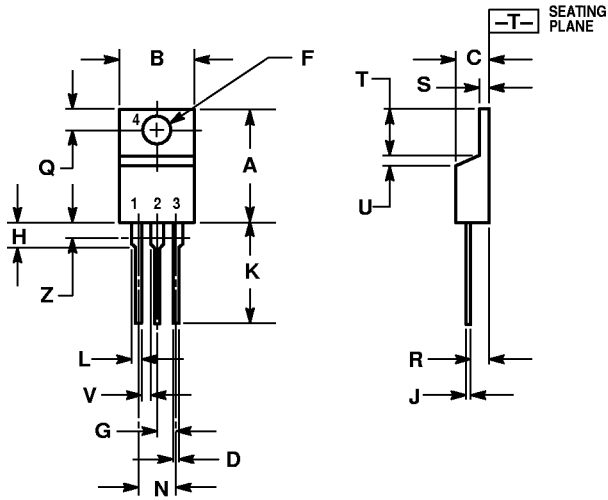


Figure 13. Effects of Base-Emitter Resistance

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:
 PIN 1: BASE
 2: COLLECTOR
 3: EMITTER
 4: COLLECTOR

CASE 221A-06
 TO-220AB
 ISSUE Y